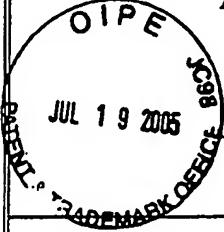


<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)				ATTY. DOCKET NO. <b>057454-0972</b>	SERIAL NO. <b>10/663,674</b>	
				<b>APPLICANT</b> <b>Hideto HIDAKA</b>		
				FILING DATE <b>September 17, 2003</b>	GROUP <b>2824</b>	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes      No
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.  
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<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)	<b>ATTY. DOCKET NO. 57454-972</b>	<b>SERIAL NO. Divisional of Appln. Serial No. 10/135,459</b>
<b>APPLICANT Hideto HIDAKA</b>		
<b>FILING DATE September 17, 2003</b>		<b>GROUP Not yet assigned</b>

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OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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